

## P-Channel 40-V (D-S), 175 °C MOSFET

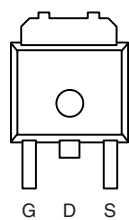
<b>PRODUCT SUMMARY</b>			
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>	$Q_g$ (Typ)
- 40	0.023 at $V_{GS} = 10$ V	- 20	20.6 nC
	0.030 at $V_{GS} = 4.5$ V	- 20	

**FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- 100 %  $R_g$  Tested

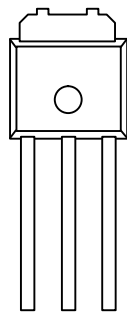

**RoHS  
COMPLIANT**
**APPLICATIONS**

- LCD TV Inverter

**TO-252**


Top View

**Order Number:**  
 SUU50P04-23-E3 (Lead (Pb)-free)

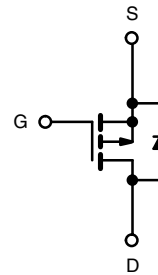
**TO-251**


Top View

**Order Number:**  
 SUU50P04-23-E3 (Lead (Pb)-free)

Drain Connected to Tab

and DRAIN-TAB



P-Channel MOSFET

**ABSOLUTE MAXIMUM RATINGS**  $T_A = 25$  °C, unless otherwise noted

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	$V_{DS}$	- 40	V	
Gate-Source Voltage	$V_{GS}$	$\pm 16$		
Continuous Drain Current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	- 20 <sup>a</sup>	
		$T_C = 100$ °C	- 20 <sup>a</sup>	
		$T_A = 25$ °C	- 8.2 <sup>b</sup>	
		$T_A = 100$ °C	- 5.7 <sup>b</sup>	
Pulsed Drain Current	$I_{DM}$	- 50	A	
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25$ °C		- 20 <sup>a</sup>
		$T_A = 25$ °C		- 2.5 <sup>b</sup>
Single Pulse Avalanche Current	$I_{AS}$	- 20	mJ	
Avalanche Energy	$E_{AS}$	20		
Maximum Power Dissipation	$P_D$	$T_C = 25$ °C	45.4	
		$T_C = 100$ °C	22.7	
		$T_A = 25$ °C	3.1 <sup>b</sup>	
		$T_A = 100$ °C	1.5 <sup>b</sup>	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 175	°C	

**THERMAL RESISTANCE RATINGS**

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b</sup>	$R_{thJA}$	40	48	°C/W
Maximum Junction-to-Case	$R_{thJC}$	2.75	3.3	

Notes:

a. Package limited.

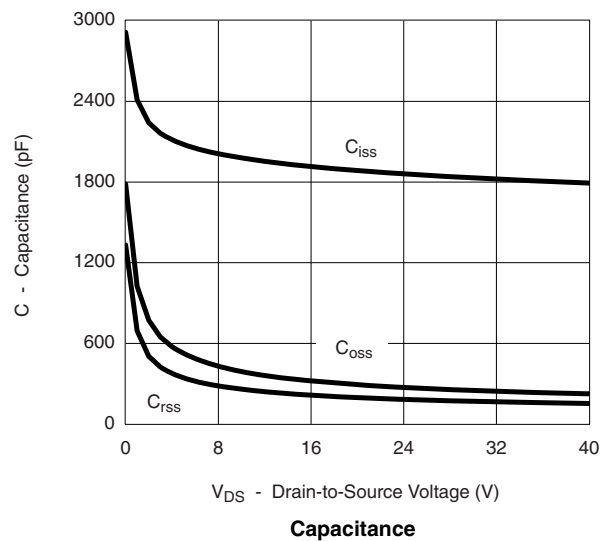
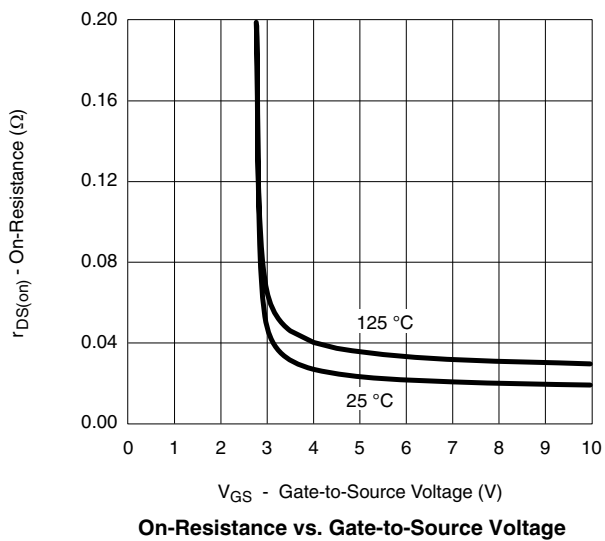
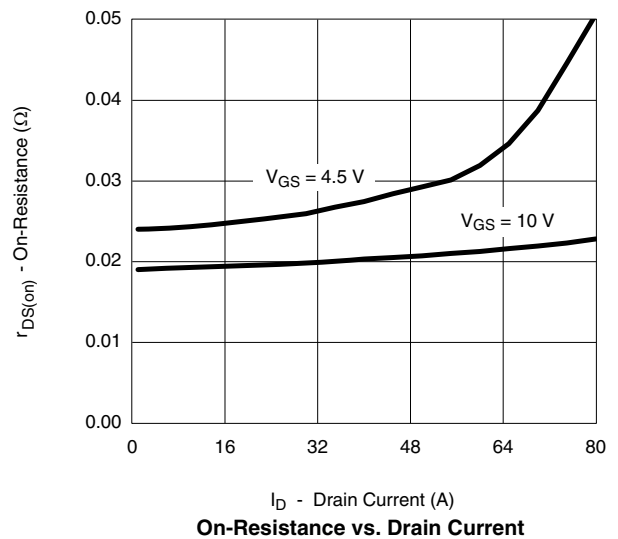
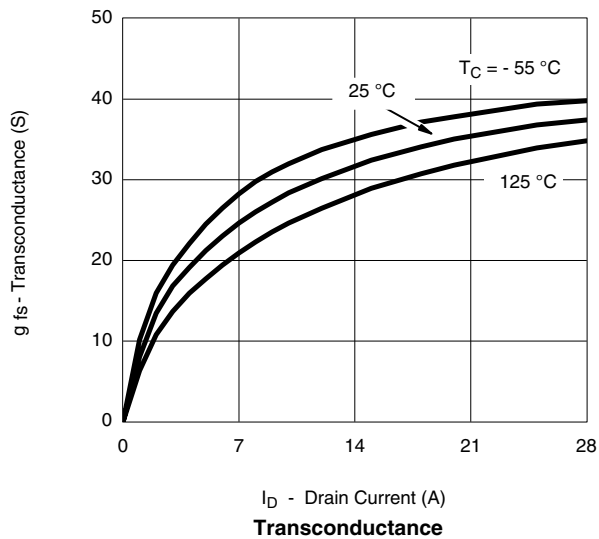
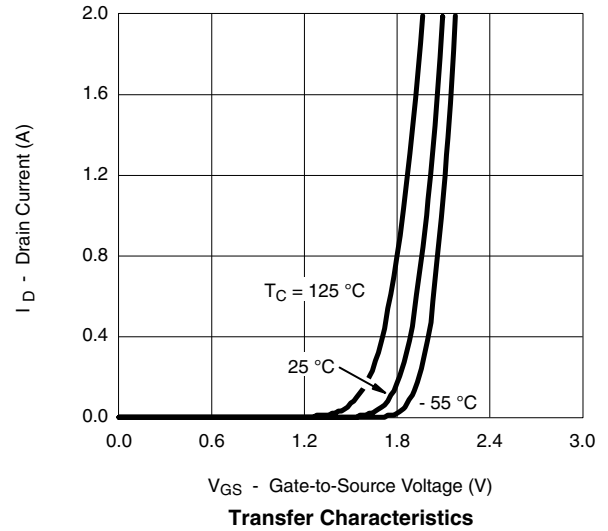
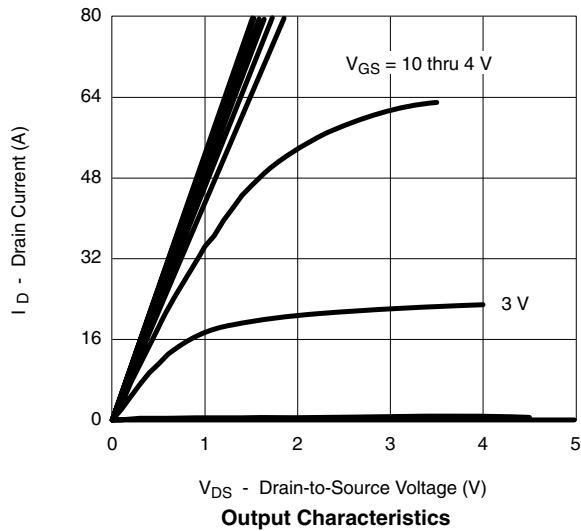
b. Surface mounted on 1" x 1" FR4 board.

<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-40			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-40		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		3.7			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.8		-2	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 16\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}, T_J = 100\text{ }^\circ\text{C}$			-20	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq -5\text{ V}, V_{GS} = -10\text{ V}$	-30			A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -15\text{ A}$		0.019	0.023	$\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -10\text{ A}$		0.024	0.030	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = -15\text{ A}$		30		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1880		pF
Output Capacitance	$C_{oss}$		286			
Reverse Transfer Capacitance	$C_{rss}$		192			
Total Gate Charge	$Q_g$	$V_{DS} = -20\text{ V}, V_{GS} = -10\text{ V}, I_D = -30\text{ A}$		43.5	65	nC
			20.6	31		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -20\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -30\text{ A}$		4.6		nC
Gate-Drain Charge	$Q_{gd}$		7.6			
Gate Resistance	$R_g$		$f = 1\text{ MHz}$		3	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -20\text{ V}, R_L = 0.66\text{ }\Omega$ $I_D \cong -30\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		22	35	ns
Rise Time	$t_r$		217	325		
Turn-Off Delay Time	$t_{d(off)}$		42	65		
Fall Time	$t_f$		21	32		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -20\text{ V}, R_L = 0.66\text{ }\Omega$ $I_D \cong -30\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		8	15	ns
Rise Time	$t_r$		12	20		
Turn-Off Delay Time	$t_{d(off)}$		36	55		
Fall Time	$t_f$		9	15		
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			-20	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				-50	
Body Diode Voltage	$V_{SD}$	$I_S = -10\text{ A}$		-0.85	-1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = -20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		44	66	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		53	80	nC	
Reverse Recovery Fall Time	$t_a$		18		ns	
Reverse Recovery Rise Time	$t_b$		26			

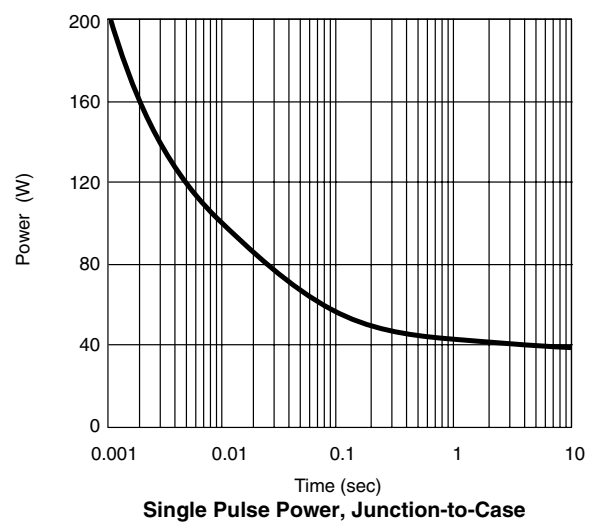
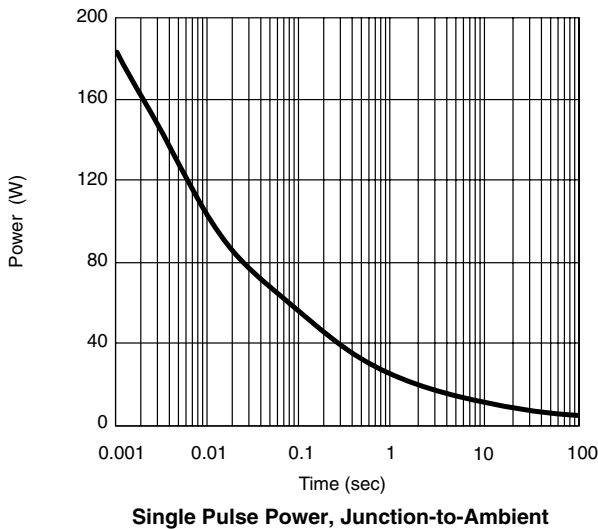
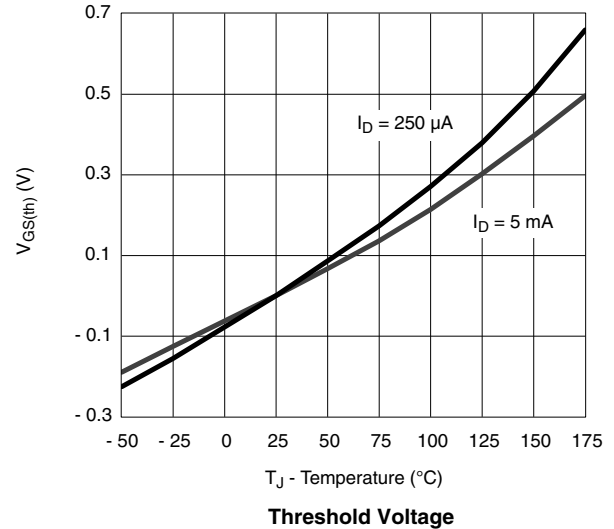
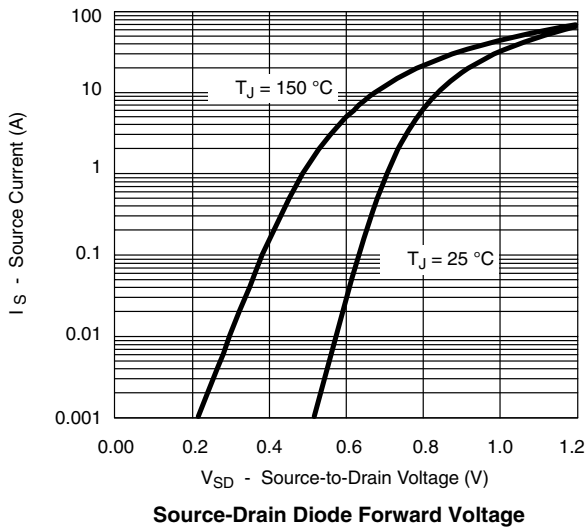
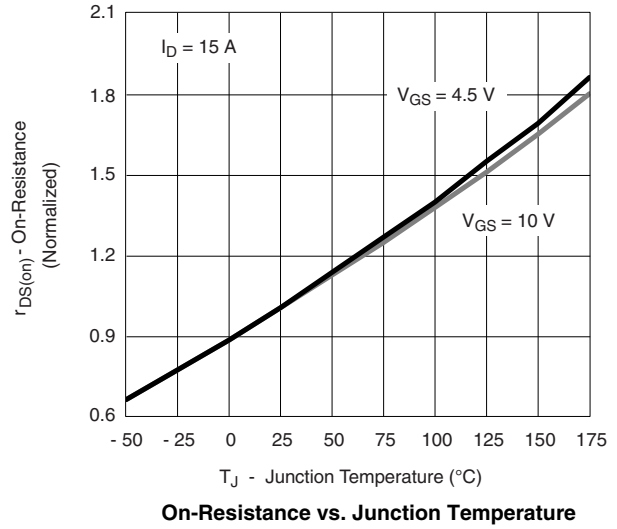
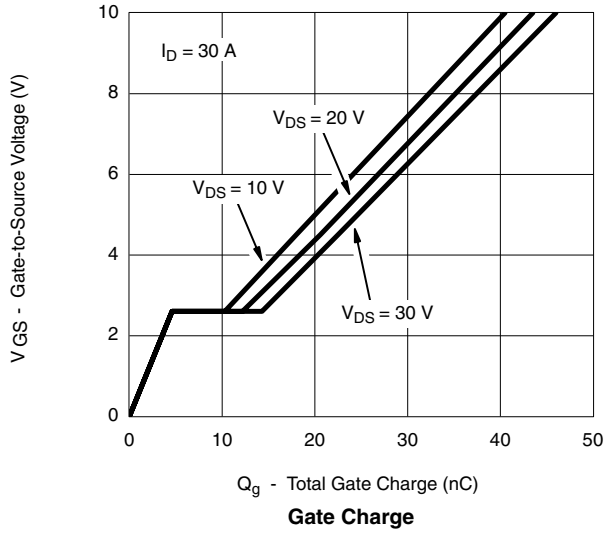
Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

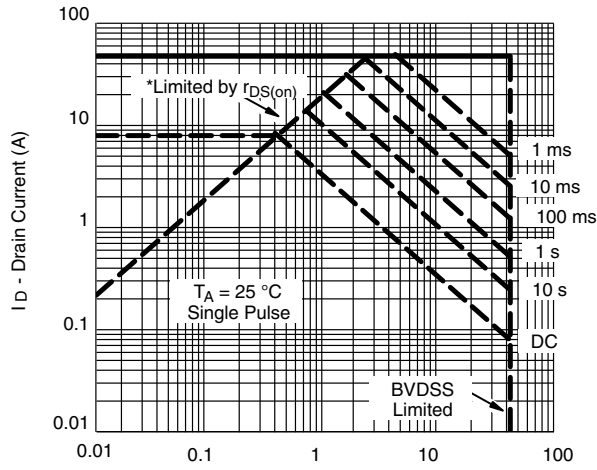
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


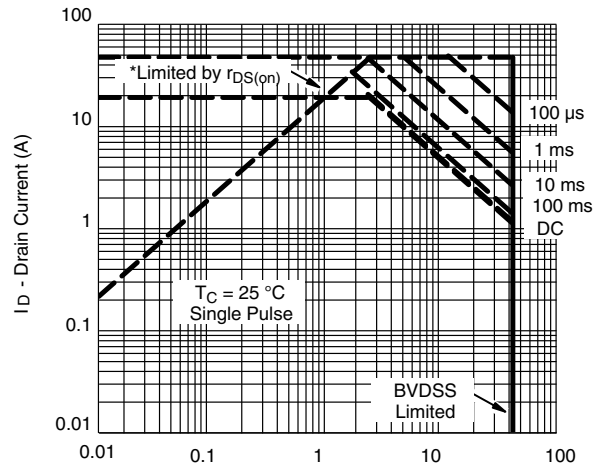
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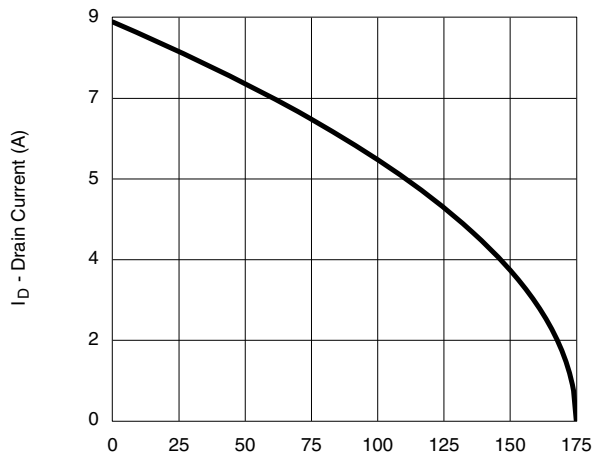
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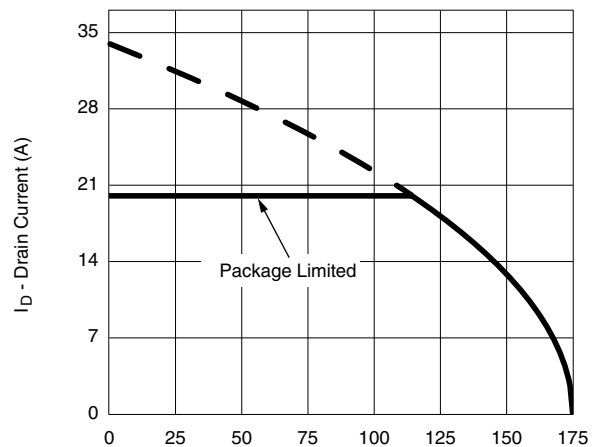
$V_{DS}$  - Drain-to-Source Voltage (V)  
 \* $V_{GS} >$  minimum  $V_{GS}$  at which  $r_{DS(on)}$  is specified  
**Safe Operating Area, Junction-to-Ambient**



$V_{DS}$  - Drain-to-Source Voltage (V)  
 \* $V_{GS} >$  minimum  $V_{GS}$  at which  $r_{DS(on)}$  is specified  
**Safe Operating Area, Junction-to-Case**

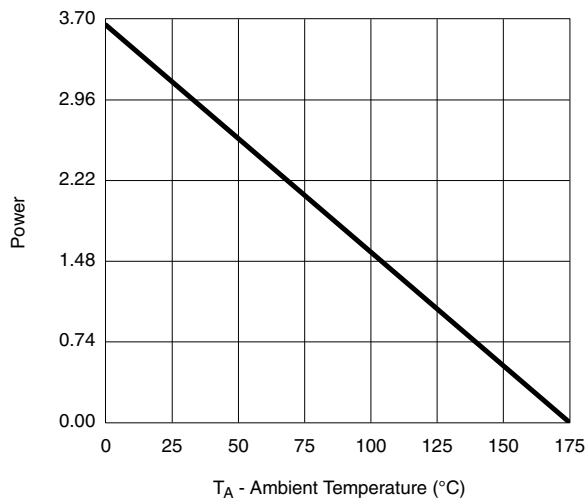


$T_A$  - Ambient Temperature (°C)  
**Current Derating\*, Junction-to-Ambient**

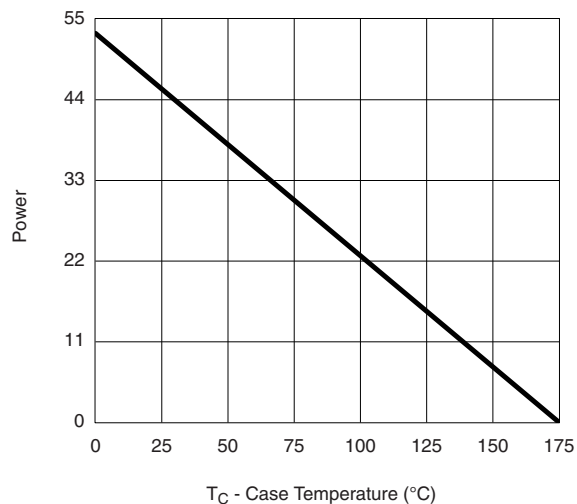


$T_A$  - Ambient Temperature (°C)  
**Current Derating\*, Junction-to-Case**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



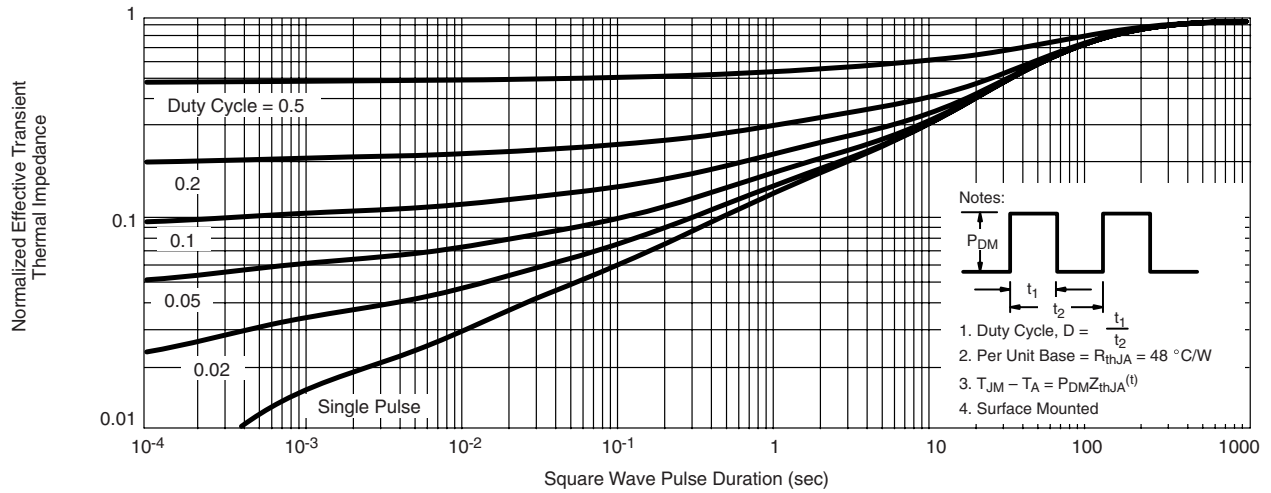
**Power Derating\*, Junction-to-Ambient**



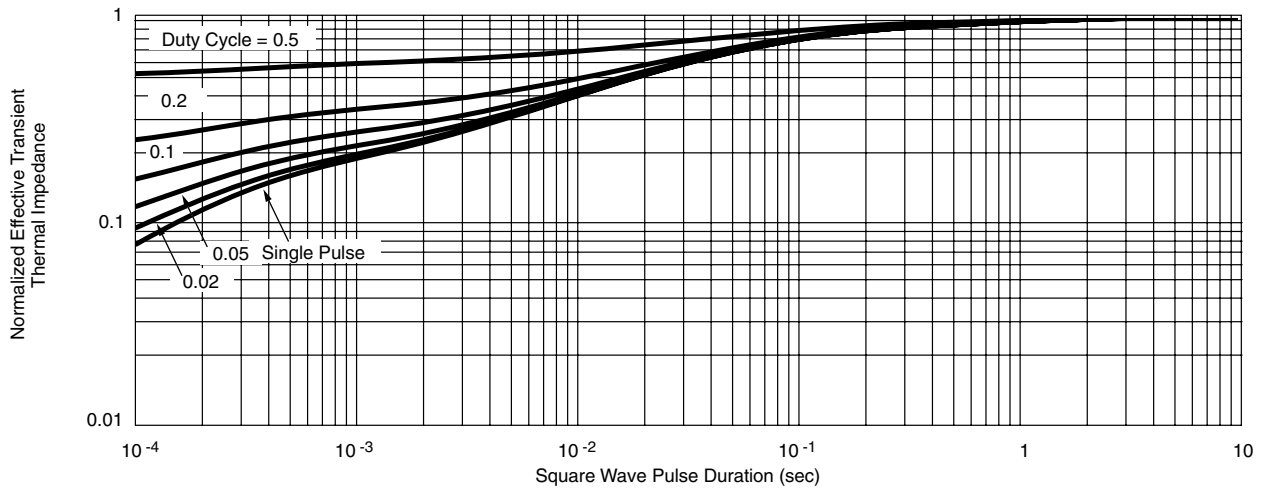
**Power Derating\*, Junction-to-Case**

\*The power dissipation  $P_D$  is based on  $T_{J(max)} = 175\text{ °C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Case**

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